



Substitute for FORM PTO-8A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet

1

of

Complete If Known	
Application Number	10/763,018
Filing Date	January 21, 2004
First Named Inventor	Tan, Zhengquan
Art Unit	2812
Examiner Name	Unassigned
Attorney Docket Number	016301-042210US

U.S. PATENT DOCUMENTS+					
Examiner Initials*	Cite No. ¹	Document Number Number Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
MRC	AA	4,667,365	05-26-1987	Martinek	
	AB	4,690,746	09-01-1987	McInerney et al.	
	AC	4,737,379	04-12-1988	Hudgens et al.	
	AD	4,835,005	05-30-1989	Hirooka et al.	
	AE	4,890,575	01-02-1990	Ito et al.	
	AF	4,894,352	01-16-1990	Lane et al.	
	AG	5,013,691	05-07-1991	Lory et al.	
	AH	5,571,571	11-05-1996	Musaka et al.	
	AI	5,571,576	11-05-1996	Qian et al.	
	AJ	5,645,645	07-08-1997	Zhang et al.	
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	AL	5,719,085	02-17-1998	Moon et al.	
	AM	5,728,621	03-17-1998	Zheng et al.	
	AN	5,750,211	05-12-1998	Weise et al.	
	AO	5,804,259	09-08-1998	Robles	
	AP	5,872,058	02-16-1999	Van Cleempot et al.	
	AQ	5,872,058	02-16-1999	Van Cleempot et al.	
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	AS	5,976,327	11-02-1999	Tanaka	
	AT	5,990,013	11-23-1999	Berenguer et al.	
	AU	6,013,191	01-11-2000	Nasser-Faili et al.	
	AV	6,013,584	01-11-2000	M'Saad	
	AW	6,020,458	02-01-2000	Lee et al.	
	AX	6,030,881	02-29-2000	Papasouliotis et al.	
	AY	6,039,851	03-21-2000	Iyer	
	AZ	6,051,321	04-18-2000	Lee et al.	
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	BB	6,149,779	11-21-2000	Van Cleempot	
	BC	6,150,212	11-21-2000	Divakaruni et al.	
	BD	6,150,285	11-21-2000	Besser et al.	
	BE	6,194,038	02-27-2001	Rossman	
	BF	6,194,038 B1	02-27-2001	Rossman	

Examiner Signature

Date Considered

10/7/04

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² Kind Codes of U.S. Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

Substitute for form 1449A/PTO				Complete if Known	
				Application Number	10/763,018
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Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
MM	BG	6,197,691		03-06-2001	Lee	
	BH	6,217,658 B1		04-17-2001	Orczyk et al.	
	BI	6,228,751 B1		05-08-2001	Yamazaki et al.	
	BJ	6,258,407 B1		07-10-2001	Lee et al.	
	BK	6,268,297 B1		07-31-2001	Nag et al.	
	BL	6,313,010 B1		11-06-2001	Nag et al.	
	BM	6,355,581 B1		03-12-2002	Vassiliev et al.	
MM	BN	6,395,150 B1		05-28-2002	Van Cleemput et al.	

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)				
MM	BO	EP	0 822 585	A2	02-04-1998	Applied Materials		<input type="checkbox"/>
MM	BP	JP	2-58836	A	02-28-1990			<input type="checkbox"/>
MM	BQ	JP	7-161703	A	06-23-1995			<input type="checkbox"/>
MM	BR	GB	2 267 291	A	12-01-1993			<input type="checkbox"/>
								<input type="checkbox"/>
								<input type="checkbox"/>
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Substitute for form 1449B/PTO				Complete If Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				<i>Application Number</i>	10/763,018
				<i>Filing Date</i>	January 21, 2004
				<i>First Named Inventor</i>	Tan, Zhengquan
				<i>Art Unit</i>	2812
				<i>Examiner Name</i>	Unassigned
Sheet	3	of		<i>Attorney Docket Number</i>	016301-042210US

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
<i>YV</i>	BS	V.Y. Vassiliev et al., "Trends in Void Free Pre-metal CVD Dielectrics," <i>Solid State Technology</i> , pp. 129-136 (March 2001).			
	BT	L.Q. Qian et al., "High Density Plasma Deposition and Deep Submicron Gap Fill with Low Dielectric Constant SiOF Films," <i>February 21-22, 1995 DUMIC Conference</i> , pp. 50-56 (February 1995).			
	BU	T. Fukada et al., "Preparation of SiOF with Low Dielectric Constant by ECR Plasma CVD," <i>February 21-22, 1995 DUMIC Conference</i> , pp. 43-49 (February 1995).			
	BV	D. Yu et al., "Step Coverage Study of PETEOS Deposition for Intermetal Dielectric Applications," <i>June 12-13, 1990 VMIC Conference</i> , pp. 166-172 (June 1990).			
	BW	K. Musaka et al., "Single Step Gap Filling Technology for Subhalf Micron Metal Spacings on Plasma Enhanced TEOS/O ₂ Chemical Vapor Deposition System," <i>Extended Abstracts of the 1993 International Conference on Solid State Devices and Materials, Makuhari</i> , pp. 510-512 (1993).			
	BX	T. Fukuda et al., "Highly Reliable SiOF Film Formation Using High Density Plasma Containing Hydrogen," <i>February 10-11, 1997 DUMIC Conference</i> , pp. 41-49 (February 1997).			
	BY	G.Y. LEE et al., "A Low Redeposition Rate High Density Plasma CVD Process for High Aspect Ratio 175 mm Technology and Beyond," <i>Proceedings of IEEE 1999 International Interconnect Technology Conference</i> , pp. 152-154 (1999).			
	BZ	V.Y. Vassiliev et al., "Properties and Gap-Fill Capability of HDP-CVD Phosphosilicate Glass Films for Subquarter-Micrometer ULSI Device Technology," <i>Electrochemical and Solid-State Letters</i> , vol. 3, no. 2, pp. 80-83 (2000).			
	CA	NALWA, H.S., <i>Handbook of Low and High Dielectric Constant Materials and Their Applications</i> , vol. 1, page 66 (1999).			
<i>YV</i>	CB	NGUYEN, s.v., "High-Density Plasma Chemical Vapor Deposition of Silicon-Based Dielectric Films for Integrated Circuits," <i>Journal of Research and Development</i> , vol. 43, 1/2 (1999).			

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